

Attorney Docket No. 59521 (48229)

N THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Hiroyuki Shimada EXAMINER: Chen Kin Chan

U.S.S.N.:

10/678,994

GROUP ART UNIT: 1765

FILED:

October 3, 2003

CONFIRMATION NO.: 8918

FOR: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE INCLUDING ETCHING A CONDUCTIVE LAYER BY USING A GAS

INCLUDING SiCl₄ and NF₃

CERTIFICATE OF EXPRESS MAILING (Label No.: EV 654389293 US)

I hereby certify that this correspondence is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 C.F.R. section 1.10, on <u>September 22, 2005</u> and is addressed to: Mail Stop AMENDMENT, Commissioner for Patents, P.O. Box 1450, Arlington, VA 22313-1450.

Nicole M. McKinnon

Mail Stop AMENDMENT Commissioner for Patents P.O. Box 1450 Arlington, VA 22313-1450

Sir:

AMENDMENT UNDER 37 C.F.R. § 1.111

In response to the Office Action dated June 20, 2005, Applicant submits the following amendment.

Amendment Under 37 C.F.R. § 1.111

U.S.S.N.: 10/678,994

Page 2 of 9

IN THE TITLE:

Please change the title to the following title:

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE INCLUDING ETCHING A CONDUCTIVE LAYER BY USING A GAS INCLUDING SiCl4 and $${\rm NF}_3$$